

Dual General Purpose Transistor

NST3904DXV6T1G, NSVT3904DXV6T1G, NST3904DXV6T5G

The NST/NSV3904DXV6 device is a spin-off of our popular SOT-23/SOT-323 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-563 six-leaded surface mount package. By putting two discrete devices in one package, this device is ideal for low-power surface mount applications where board space is at a premium.

Features

- h_{FE} , 100–300
- Low $V_{CE(sat)}$, ≤ 0.4 V
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- AEC-Q101 Qualified and PPAP Capable – NSVT3904DXV6T1G
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements

MAXIMUM RATINGS

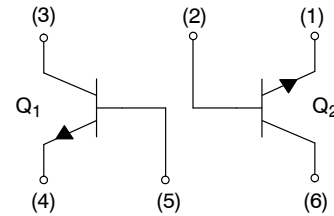
Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	40	Vdc
Collector–Base Voltage	V_{CBO}	60	Vdc
Emitter–Base Voltage	V_{EBO}	6.0	Vdc
Collector Current – Continuous	I_C	200	mAdc
Electrostatic Discharge	HBM MM	ESD >16000 >2000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



ON Semiconductor®

www.onsemi.com

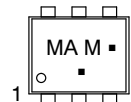


NST/NSV3904DXV6



SOT-563
CASE 463A
STYLE 1

MARKING DIAGRAM



MA = Device Code

M = Date Code

▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NST3904DXV6T1G	SOT-563 (Pb-Free)	4000/Tape & Reel
NSVT3904DXV6T1G	SOT-563 (Pb-Free)	4000/Tape & Reel
NST3904DXV6T5G	SOT-563 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NST3904DXV6T1G, NSVT3904DXV6T1G, NST3904DXV6T5G

THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C (Note 1)	P_D	357 2.9	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	350	$^\circ\text{C}/\text{W}$
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C (Note 1)	P_D	500 4.0	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	250	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-4 @ Minimum Pad

NST3904DXV6T1G, NSVT3904DXV6T1G, NST3904DXV6T5G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (Note 2) (I _C = 1.0 mAdc, I _B = 0)	V _{(BR)CEO}	40	–	Vdc
Collector – Base Breakdown Voltage (I _C = 10 μAdc, I _E = 0)	V _{(BR)CBO}	60	–	Vdc
Emitter – Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0)	V _{(BR)EBO}	6.0	–	Vdc
Base Cutoff Current (V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)	I _{BL}	–	50	nAdc
Collector Cutoff Current (V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)	I _{CEX}	–	50	nAdc

ON CHARACTERISTICS (Note 2)

DC Current Gain (I _C = 0.1 mAdc, V _{CE} = 1.0 Vdc) (I _C = 1.0 mAdc, V _{CE} = 1.0 Vdc) (I _C = 10 mAdc, V _{CE} = 1.0 Vdc) (I _C = 50 mAdc, V _{CE} = 1.0 Vdc) (I _C = 100 mAdc, V _{CE} = 1.0 Vdc)	h _{FE}	40 70 100 60 30	– – 300 – –	–
Collector – Emitter Saturation Voltage (I _C = 10 mAdc, I _B = 1.0 mAdc) (I _C = 50 mAdc, I _B = 5.0 mAdc)	V _{CE(sat)}	– –	0.2 0.3	Vdc
Base – Emitter Saturation Voltage (I _C = 10 mAdc, I _B = 1.0 mAdc) (I _C = 50 mAdc, I _B = 5.0 mAdc)	V _{BE(sat)}	0.65 –	0.85 0.95	Vdc

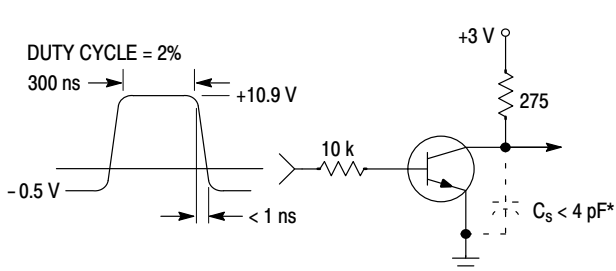
SMALL – SIGNAL CHARACTERISTICS

Current – Gain – Bandwidth Product (I _C = 10 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	f _T	300	–	MHz
Output Capacitance (V _{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	–	4.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	–	8.0	pF
Input Impedance (V _{CE} = 10 Vdc, I _C = 1.0 mAdc, f = 1.0 kHz)	h _{ie}	1.0 2.0	10 12	k Ω
Voltage Feedback Ratio (V _{CE} = 10 Vdc, I _C = 1.0 mAdc, f = 1.0 kHz)	h _{re}	0.5 0.1	8.0 10	X 10 ⁻⁴
Small – Signal Current Gain (V _{CE} = 10 Vdc, I _C = 1.0 mAdc, f = 1.0 kHz)	h _{fe}	100 100	400 400	–
Output Admittance (V _{CE} = 10 Vdc, I _C = 1.0 mAdc, f = 1.0 kHz)	h _{oe}	1.0 3.0	40 60	μmhos
Noise Figure (V _{CE} = 5.0 Vdc, I _C = 100 μAdc, R _S = 1.0 k Ω, f = 1.0 kHz)	NF	– –	5.0 4.0	dB

SWITCHING CHARACTERISTICS

Delay Time	(V _{CC} = 3.0 Vdc, V _{BE} = –0.5 Vdc)	t _d	–	35	ns
Rise Time	(I _C = 10 mAdc, I _{B1} = 1.0 mAdc)	t _r	–	35	
Storage Time	(V _{CC} = 3.0 Vdc, I _C = 10 mAdc)	t _s	–	200	ns
Fall Time	(I _{B1} = I _{B2} = 1.0 mAdc)	t _f	–	50	

2. Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2.0%.



* Total shunt capacitance of test jig and connectors

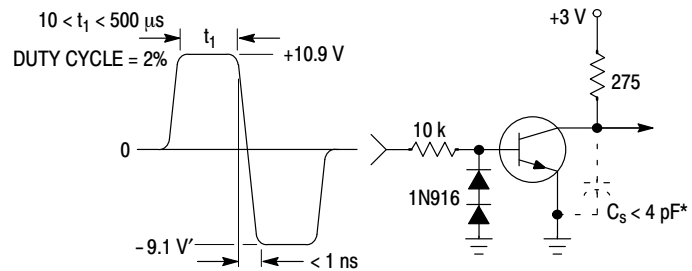


Figure 1. Delay and Rise Time Equivalent Test Circuit

Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS

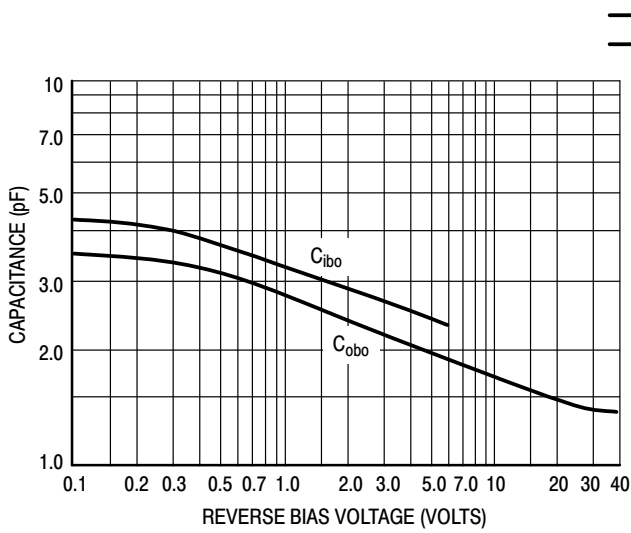


Figure 3. Capacitance

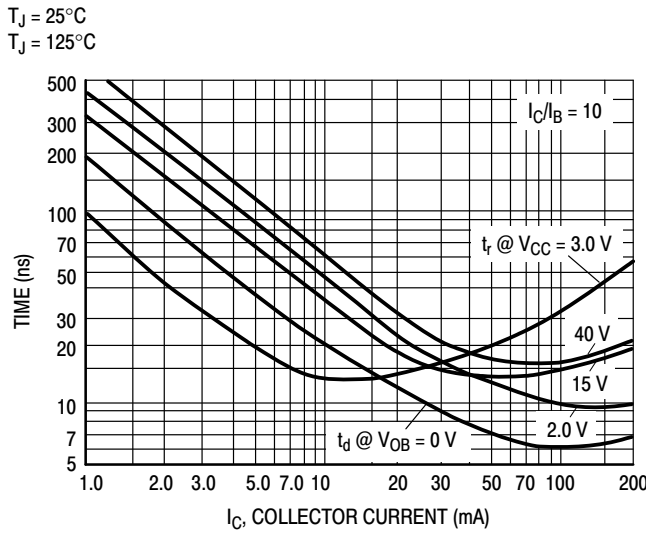


Figure 4. Turn-On Time

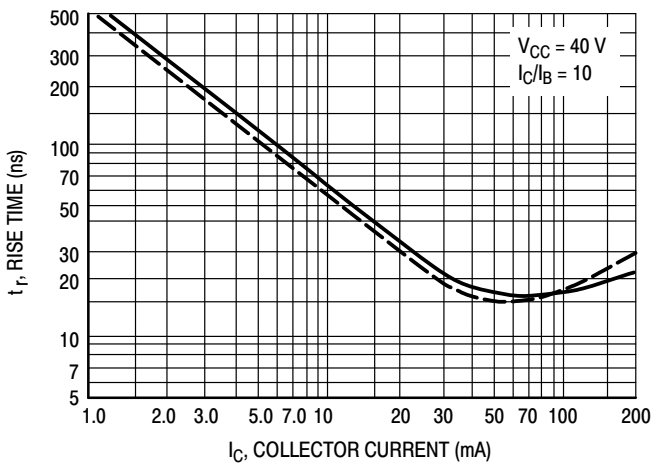


Figure 5. Rise Time

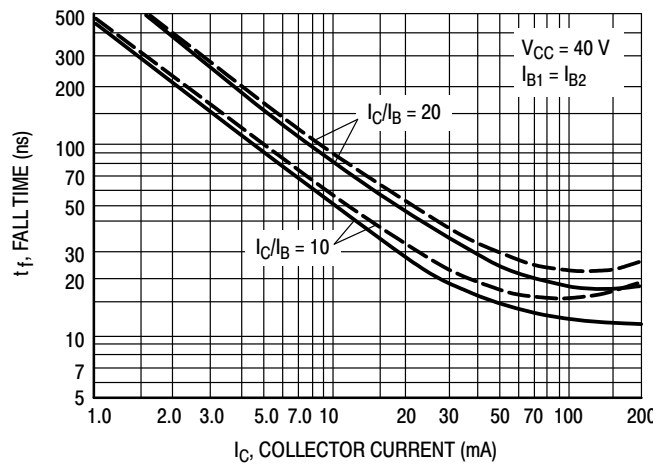


Figure 6. Fall Time

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS
NOISE FIGURE VARIATIONS

($V_{CE} = 5.0$ Vdc, $T_A = 25^\circ\text{C}$, Bandwidth = 1.0 Hz)

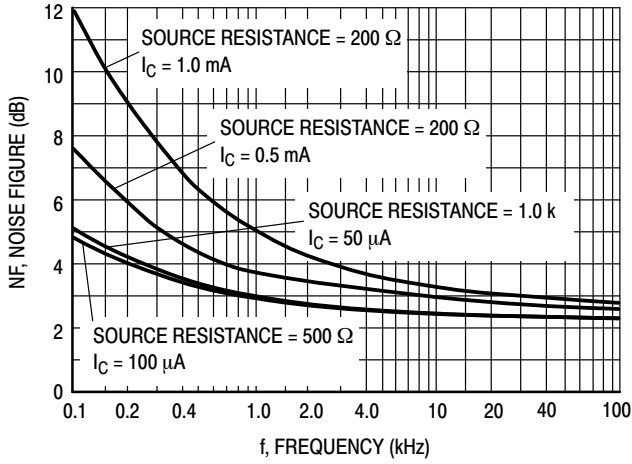


Figure 7. Noise Figure

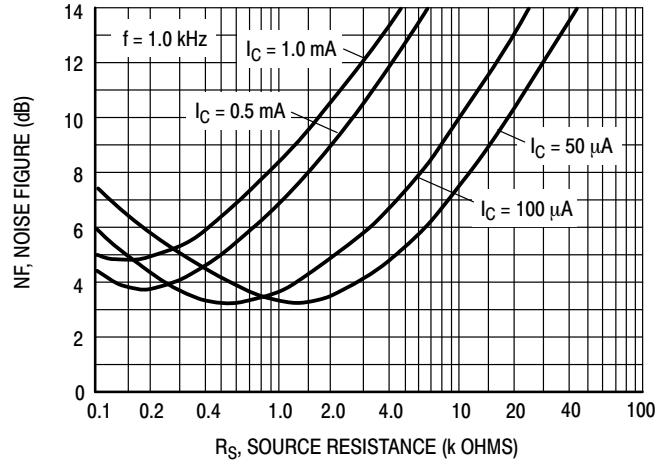


Figure 8. Noise Figure

h PARAMETERS

($V_{CE} = 10$ Vdc, $f = 1.0$ kHz, $T_A = 25^\circ\text{C}$)

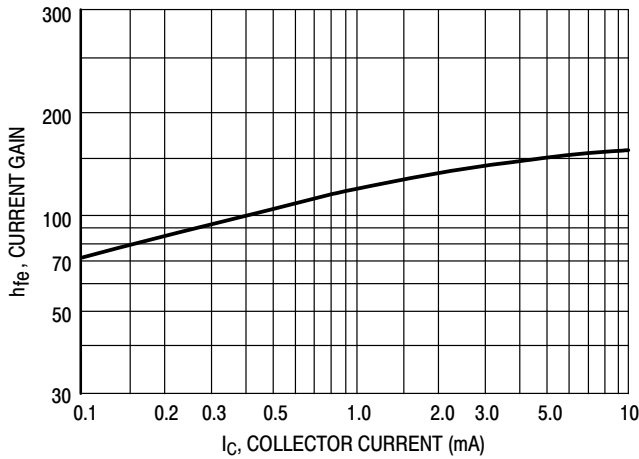


Figure 9. Current Gain

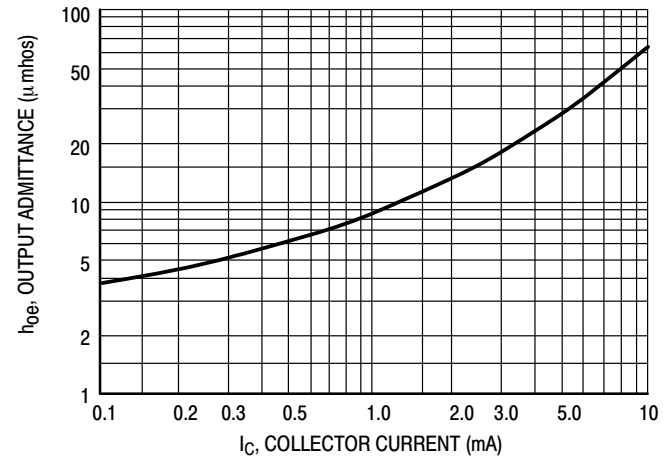


Figure 10. Output Admittance

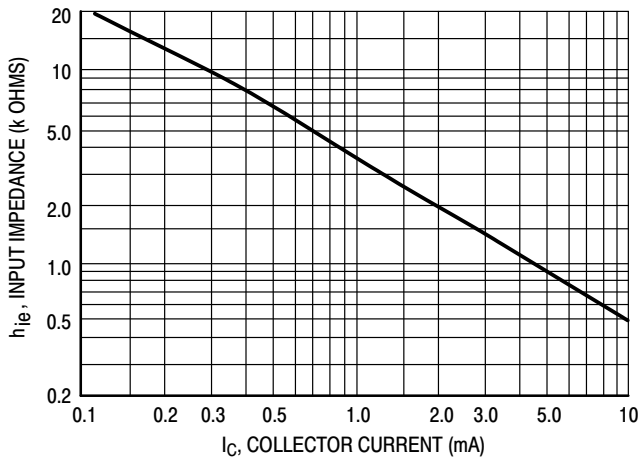


Figure 11. Input Impedance

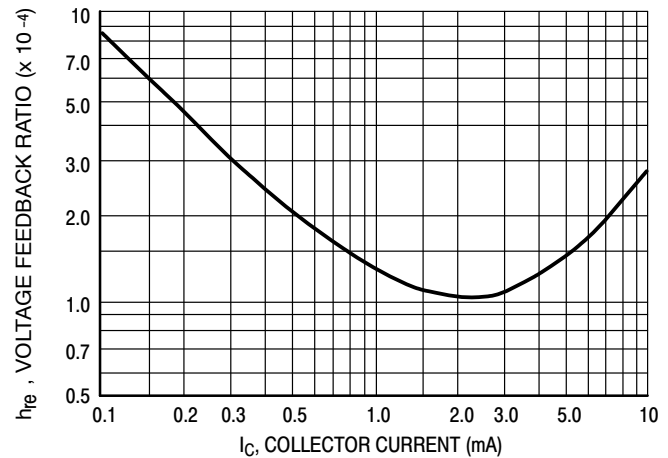


Figure 12. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

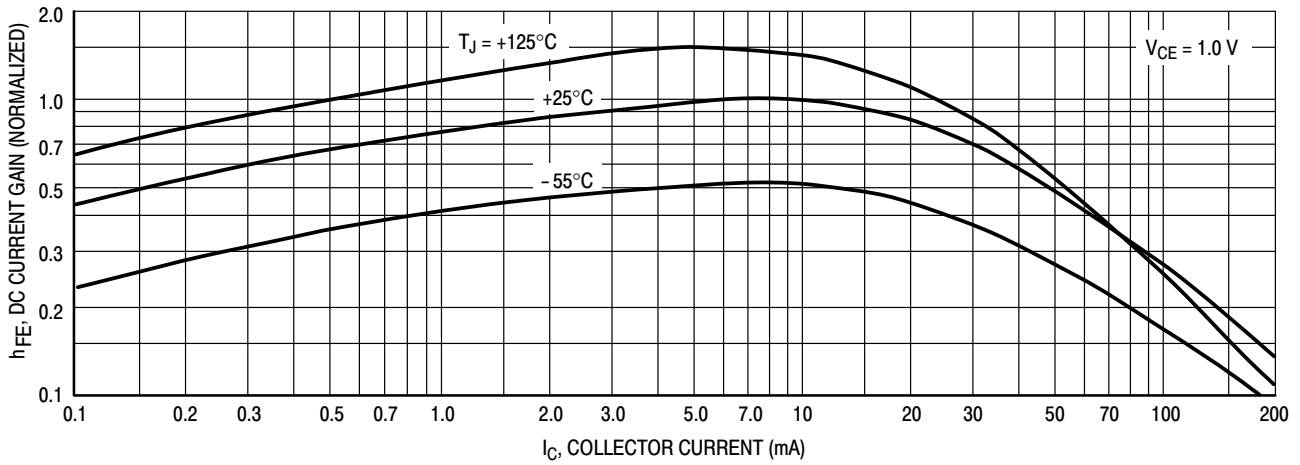


Figure 13. DC Current Gain

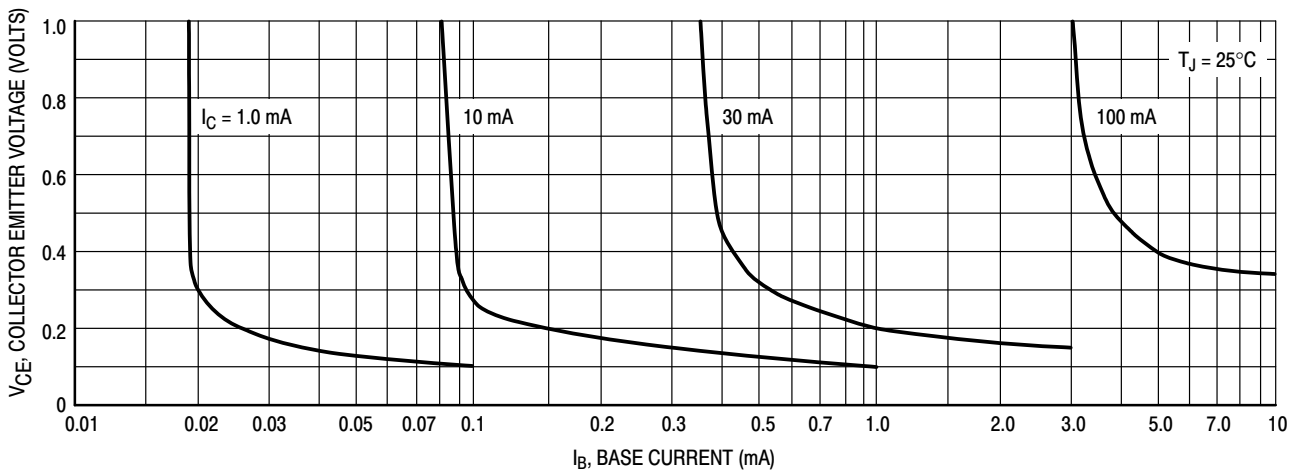


Figure 14. Collector Saturation Region

TYPICAL STATIC CHARACTERISTICS

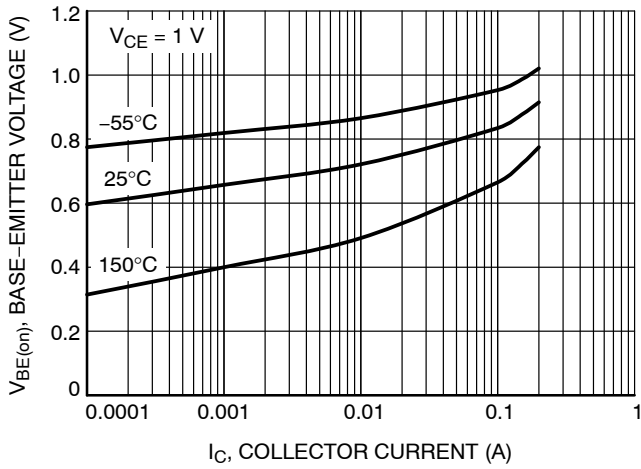


Figure 15. Base Emitter Voltage vs. Collector Current

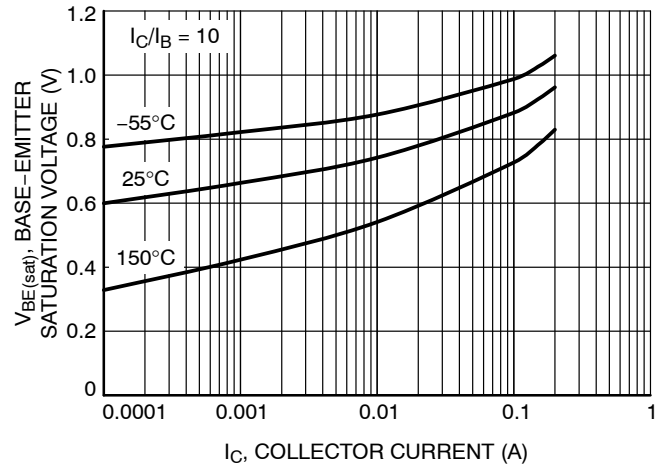


Figure 16. Base Emitter Saturation Voltage vs. Collector Current

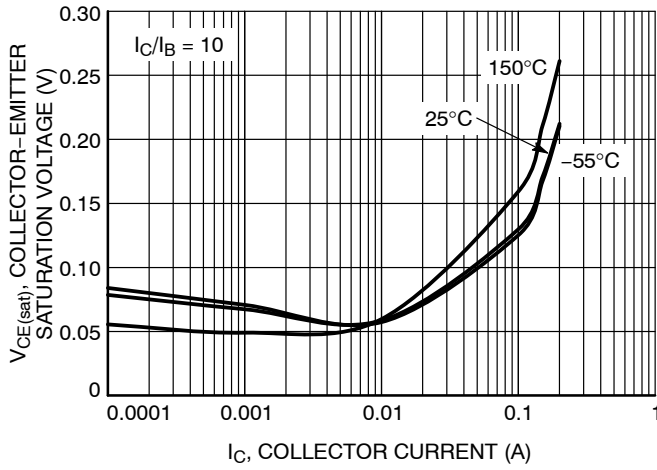


Figure 17. Collector Emitter Saturation Voltage vs. Collector Current

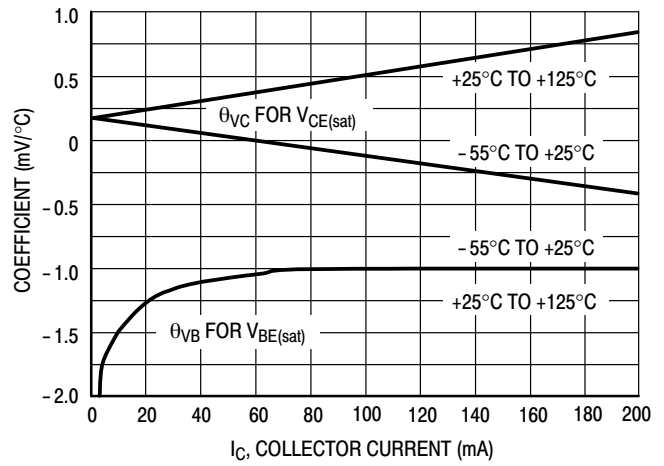


Figure 18. Temperature Coefficients

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 4:1

SOT-563, 6 LEAD
CASE 463A
ISSUE H

DATE 26 JAN 2021

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.50	0.55	0.60
b	0.17	0.22	0.27
c	0.08	0.13	0.18
D	1.50	1.60	1.70
E	1.10	1.20	1.30
e	0.50 BSC		
L	0.10	0.20	0.30
H _E	1.50	1.60	1.70

RECOMMENDED MOUNTING FOOTPRINT*

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON11126D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOT-563, 6 LEAD	PAGE 1 OF 2

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

SOT-563, 6 LEAD
CASE 463A
ISSUE H

DATE 26 JAN 2021

STYLE 1:
PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1

STYLE 2:
PIN 1. EMITTER 1
2. EMITTER 2
3. BASE 2
4. COLLECTOR 2
5. BASE 1
6. COLLECTOR 1

STYLE 3:
PIN 1. CATHODE 1
2. CATHODE 1
3. ANODE/ANODE 2
4. CATHODE 2
5. CATHODE 2
6. ANODE/ANODE 1

STYLE 4:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE
4. ANODE
5. CATHODE
6. CATHODE

STYLE 6:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE

STYLE 8:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

STYLE 9:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

STYLE 10:
PIN 1. CATHODE 1
2. N/C
3. CATHODE 2
4. ANODE 2
5. N/C
6. ANODE 1

STYLE 11:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

**GENERIC
MARKING DIAGRAM***



XX = Specific Device Code
M = Month Code
■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98AON11126D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOT-563, 6 LEAD	PAGE 2 OF 2

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT

North American Technical Support:

Voice Mail: 1 800-282-9855 Toll Free USA/Canada

Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative